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L6: Entry 1 of 4

File: USPT

Jan 19, 1999

US-PAT-NO: 5861135

DOCUMENT-IDENTIFIER: US 5861135 A

TITLE: Highly crystalline diamond

DATE-ISSUED: January 19, 1999

## INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tanabe; Keiichiro	Hyogo-ken	N/A	N/A	JPX
Fujimori; Naoji	Hyogo-ken	N/A	N/A	JPX

US-CL-CURRENT: 423/446

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw Desc	Image
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☐ 2. Document ID: US 5776552 A

L6: Entry 2 of 4

File: USPT

Jul 7, 1998

US-PAT-NO: 5776552

DOCUMENT-IDENTIFIER: US 5776552 A

TITLE: Process for the vapor phase synthesis of diamond and highly crystalline diamond

DATE-ISSUED: July 7, 1998

## INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tanabe; Keiichiro	Hyogo-ken	N/A	N/A	JPX
Fujimori; Naoji	Hyogo-ken	N/A	N/A	JPX

US-CL-CURRENT: 427/577; 117/104, 423/446

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw Desc	Image
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☐ 3. Document ID: US 5646924 A

L6: Entry 3 of 4

File: USPT

Jul 8, 1997

US-PAT-NO: 5646924

DOCUMENT-IDENTIFIER: US 5646924 A

TITLE: Recording and simultaneous verifying method of phase-changing type of information recording medium

DATE-ISSUED: July 8, 1997

## INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Nonoyama; Osamu	Yokohama	N/A	N/A	JPX
Ide; Yukio	Mishima	N/A	N/A	JPX
Harigaya; Makoto	Hiratsuka	N/A	N/A	JPX
Kageyama; Yoshiyuki	Yokohama	N/A	N/A	JPX
Deguchi; Hiroshi	Yokohama	N/A	N/A	JPX
Yamada; Katsuyuki	Mishima	N/A	N/A	JPX
Takahashi; Masaetsu	Yokohama	N/A	N/A	JPX
Iwasaki; Hiroko	Tokyo	N/A	N/A	JPX

US-CL-CURRENT: 369/53.36; 369/116, 369/275.1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw. Desc	Image
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☐ 4. Document ID: US 5270263 A

L6: Entry 4 of 4

File: USPT

Dec 14, 1993

US-PAT-NO: 5270263

DOCUMENT-IDENTIFIER: US 5270263 A

TITLE: Process for depositing aluminum nitride (AlN) using nitrogen plasma sputtering

DATE-ISSUED: December 14, 1993

## INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kim; Sung C.	Boise	ID	N/A	N/A
Yu; Chris C.	Boise	ID	N/A	N/A
Doan; Trung T.	Boise	ID	N/A	N/A

US-CL-CURRENT: 438/702; 204/192.22, 204/192.25, 438/717, 438/740, 438/761

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KWIC	Draw. Desc	Image
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Terms	Documents
((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmK)	4

Documents, starting with Document:

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Terms	Documents
((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0

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(thermal adj conductivity) and (w/cmk)[Clear](#)**Search History**

Today's Date: 3/13/2001

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L7</u>
USPT	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	4	<u>L6</u>
JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w/cmk)	0	<u>L5</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cmk)	0	<u>L4</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity) and (w adj cm adj k)	0	<u>L3</u>
PGPB,JPAB	((aluminum adj nitride) or aln) and (thermal adj conductivity)	656	<u>L2</u>
PGPB	semiconductor	0	<u>L1</u>

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Terms	Documents
((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57

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<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57	<u>L5</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or oxygen or o or oxide or carbide) and glass and substrate	124	<u>L4</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and transistor	3	<u>L3</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate	244	<u>L2</u>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide)	5301	<u>L1</u>

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Terms	Documents
(alnc or alcn or (al adj c adj n) or (al adj n adj c))	26

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(alnc or alcn or (al adj c adj n) or (al adj n adj c))	▲
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<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
JPAB	(aln c or alcn or (al adj c adj n) or (al adj n adj c))	26	<a href="#"><u>L14</u></a>
JPAB	(aln c or alcn or (al adj c adj n) or (al adj n adj c)) and glass and substrate	0	<a href="#"><u>L13</u></a>
JPAB	((aluminum adj (carb\$ or \$nitride)) or alnc or alcn or (al adj c adj n) or (al adj n adj c)) and glass and substrate and semiconductor	32	<a href="#"><u>L12</u></a>
JPAB	((aluminum adj (carb\$ or \$nitride)) or alnc or alcn or (al adj c adj n) or (al adj n adj c)) and glass and substrate	118	<a href="#"><u>L11</u></a>
JPAB	((aluminum adj oxynitride) or alno or alon or (al adj o adj n) or (al adj n adj o)) and glass and substrate	9	<a href="#"><u>L10</u></a>
JPAB	((aluminum adj oxynitride) or alno or alon) and glass and substrate	2	<a href="#"><u>L9</u></a>
JPAB	(aluminum adj oxynitride) or alno or alon and glass and substrate and semiconductor	75	<a href="#"><u>L8</u></a>
JPAB	(aluminum adj oxynitride) or alno or alon and glass and substrate	75	<a href="#"><u>L7</u></a>
JPAB	(aluminum adj oxynitride) or alno or alon	131	<a href="#"><u>L6</u></a>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and semiconductor	57	<a href="#"><u>L5</u></a>
JPAB	((aluminum adj nitride) or aln) and (carbon or oxygen or o or oxide or carbide) and glass and substrate	124	<a href="#"><u>L4</u></a>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate and transistor	3	<a href="#"><u>L3</u></a>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide) and glass and substrate	244	<a href="#"><u>L2</u></a>
JPAB	((aluminum adj nitride) or aln) and (carbon or c or oxygen or o or oxide or carbide)	5301	<a href="#"><u>L1</u></a>